

PSMN6R3-120ESQ Datasheet



DiGi Electronics Part Number P Manufacturer N Manufacturer Product Number P

Description

Detailed Description

PSMN6R3-120ESQ-DG

Nexperia USA Inc.

PSMN6R3-120ESQ

MOSFET N-CH 120V 70A I2PAK

N-Channel 120 V 70A (Tc) 405W (Tc) Through Hole I2PAK

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Manufacturer Product Number:	Manufacturer:
PSMN6R3-120ESQ	Nexperia USA Inc.
Series:	Product Status:
	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
120 V	70A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
10V	6.7mOhm @ 25A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 250μΑ	207.1 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	11384 pF @ 60 V
FET Feature:	Power Dissipation (Max):
-	405W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
ІЗРАК	TO-262-3 Long Leads, I2PAK, TO-262AA

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



PSMN6R3-120ES

N-channel 120 V 6.7 mΩ standard level MOSFET in I2PAK 8 May 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic power supply equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive
- I2PAK package for slimline adaptors & height constrained applications

3. Applications

- AC-to-DC power supply
- Synchronous rectification
- Motor control
- Slimline adaptors & chargers

4. Quick reference data

Table 1. Qu	uick reference data						
Symbol	Parameter	Conditions	ſ	Vlin	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	120	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	-	70	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	405	W
Static charac	cteristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12		4	5.7	6.7	mΩ
Dynamic cha	aracteristics				_		
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 60 V;		-	61.9	-	nC
Q _{G(tot)}	total gate charge	Fig. 14; Fig. 15		-	207.1	-	nC
Avalanche ru	uggedness	·					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \ ^{\circ}\text{C}; \text{I}_{D} = 70 \text{ A}; \\ V_{sup} \leq 120 \text{ V}; \text{ unclamped}; \text{R}_{GS} = 50 \Omega; \\ \hline \text{Fig. 3} \end{array}$		-	-	532	mJ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G C C
mb	D	drain	1 2 3 I2PAK (SOT226)	mbb076 S

6. Ordering information

Table 3.	Ordering in	formation		
Type number		Package		
		Name	Description	Version
PSMN6R	3-120ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

7. Limiting values

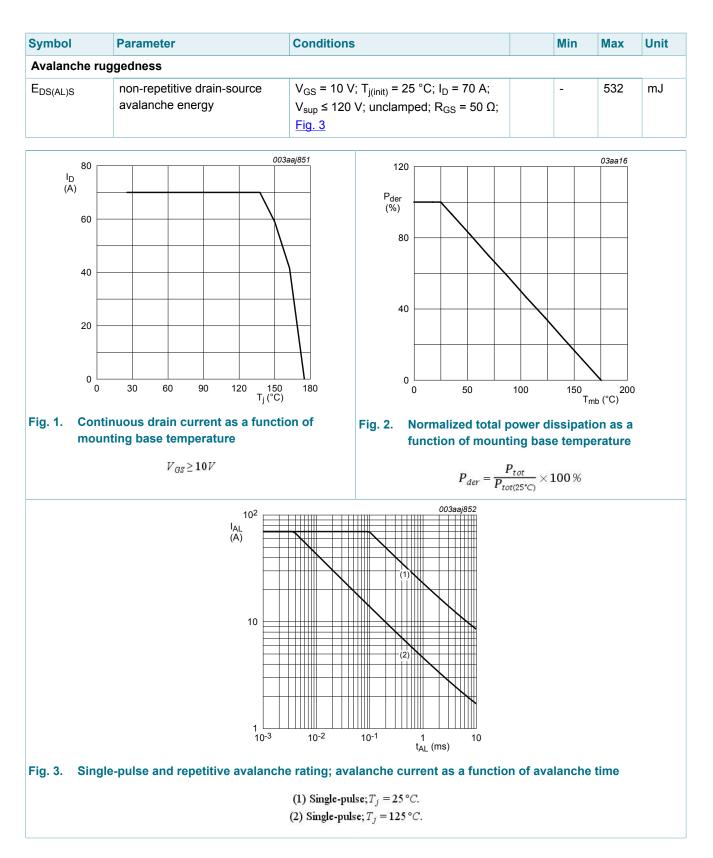
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	120	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	120	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	70	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	70	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4	-	280	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	405	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dra	in diode	· · ·			
I _S	source current	T _{mb} = 25 °C	-	70	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	280	А

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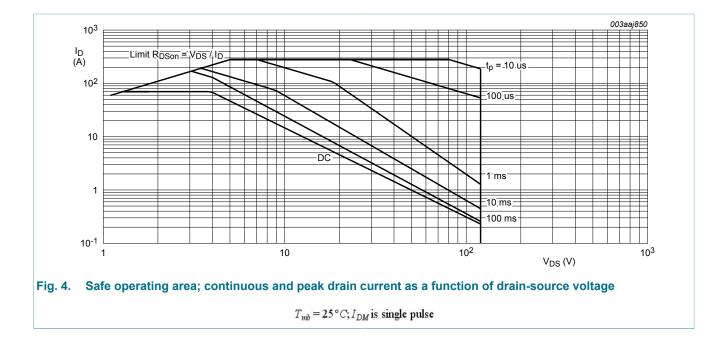
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8. Thermal characteristics

Table 5. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	0.3	0.37	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air		-	65	-	K/W



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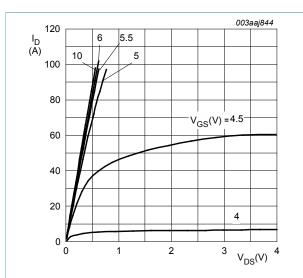
9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	120	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	108	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10; Fig. 11	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10; Fig. 11	-	-	4.6	V
I _{DSS}	drain leakage current	V_{DS} = 120 V; V_{GS} = 0 V; T_j = 25 °C	-	0.1	1	μA
		V_{DS} = 120 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	4	5.7	6.7	mΩ
	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 13; Fig. 12	-	16.5	19.4	mΩ	
R _G	internal gate resistance (AC)	f = 1 MHz	0.44	0.88	1.76	Ω
Dynamic ch	aracteristics		I			
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 60 V; V_{GS} = 10 V;	-	207.1	-	nC
Q _{GS}	gate-source charge	<u>Fig. 14; Fig. 15</u>	-	43.2	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	29.8	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	13.4	-	nC
Q _{GD}	gate-drain charge		-	61.9	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 60 V; <u>Fig. 14; Fig. 15</u>	-	4.3	-	V
C _{iss}	input capacitance	V _{DS} = 60 V; V _{GS} = 0 V; f = 1 MHz;	-	11384	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	534	-	pF
C _{rss}	reverse transfer capacitance		-	358	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 10 V;	-	42.1	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C	-	58.2	-	ns

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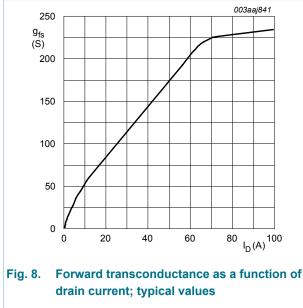
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _{d(off)}	turn-off delay time		-	142.1	-	ns
t _f	fall time	_	-	67.7	-	ns
Source-drain	n diode					
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>	-	0.79	1.2	V
t _{rr}	reverse recovery time	I_{S} = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	76.1	-	ns
Q _r	recovered charge	V _{DS} = 60 V	-	264.2	-	nC

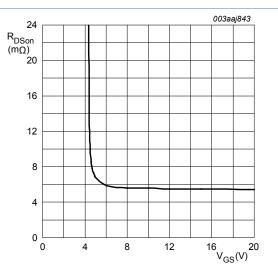




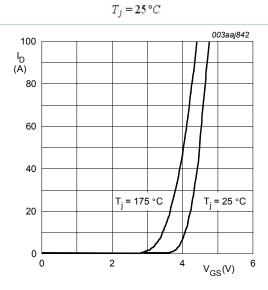




 $T_j = 25 \,^{\circ}C; V_{DS} = 10 \,^{\circ}V$





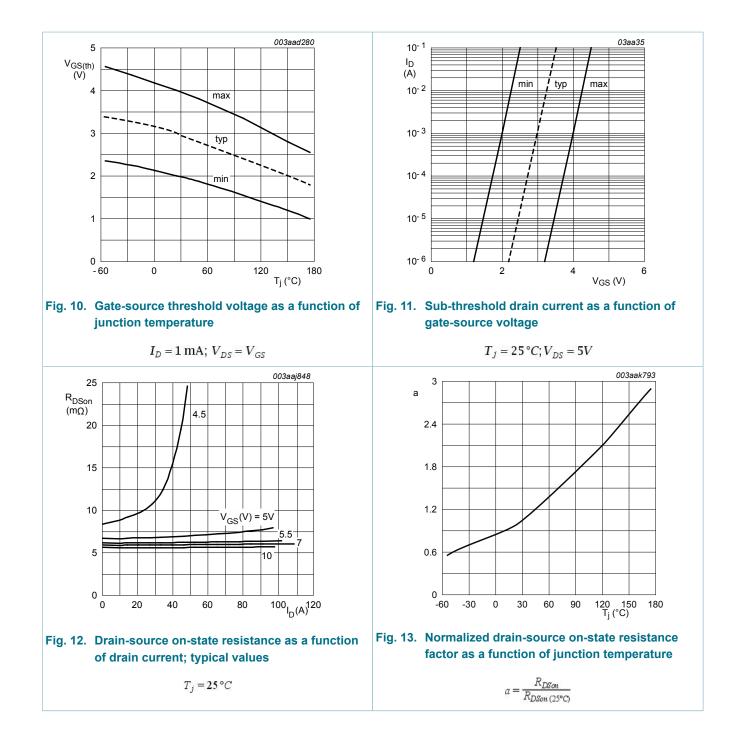




 $V_{DS} > I_D \times R_{DSon}$

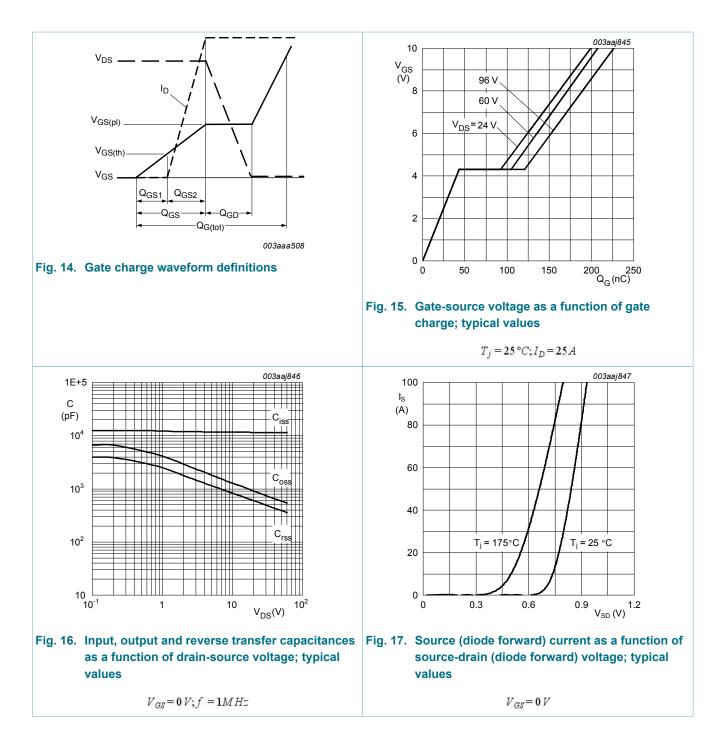
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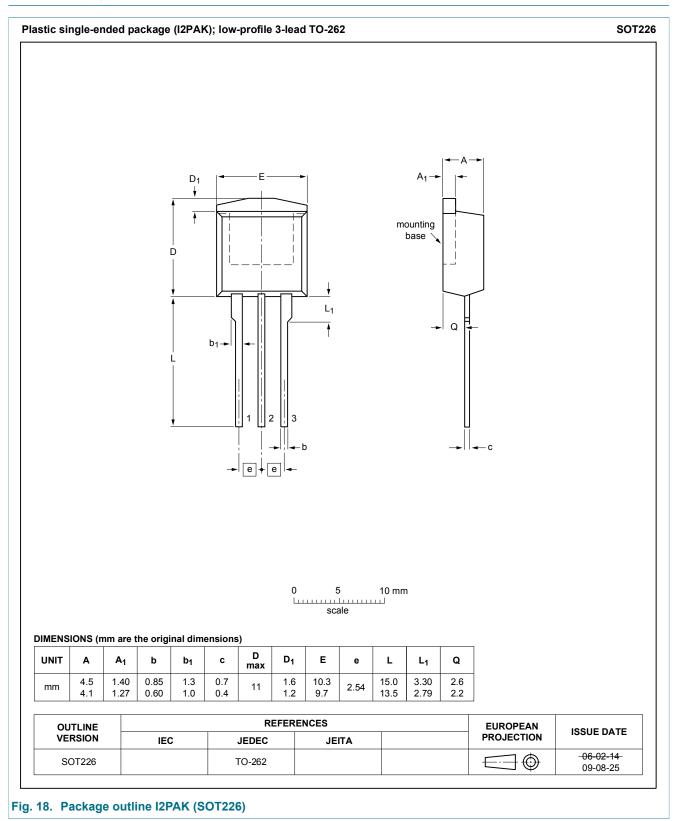
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10. Package outline



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11. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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